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Current trends in flash memory technology: invited paper

PDF from arxiv.org

Sh. Min. • Proceedings of the 2006 Asia and South Pacific ..., 2006 - portal.acm.org
... memory drives. Of course, multiple **flash** memory buses can be used for higher bus bandwidth but this approach will require a higher pin count and a bus **interleaving** logic within the **flash** memory controller. A preferred approach ...

Cited by 10 • Published online • All 2 versions

Flash memory including a mode register for indicating synchronous or asynchronous mode of operation

DR. Ming, BL. Dupert, B. Sambandam. • US Patent ..., 2000 - Google Patents

... Alternatively, if a single address is provided to the **flash** chip when it is in the synchronous mode, the subsequent addresses for the burst will be generated **within** the **flash** chip and the data burst will then be provided as output from the **flash** chip. ...

Cited by 120 • Published online • All 2 versions

Unified re-map and cache-index table with dual write-counters for wear-leveling of non-volatile flash

RAM mass storage

BR. Bruce, RH. Bruce, ET. Cohen. • US Patent 8,000,666, 1999 - Google Patents

... 7,199 [54] UNIFIED RE-MAP AND CACHE-INDEX TABLE WITH DUAL WRITE-COUNTERS FOR WEAR-LEVELING OF NON-VOLATILE FLASH RAM MASS STORAGE [75] Inventors: Ricardo H. Bruce, Union City; Rolando H. Bruce, South San Francisco; Earl T. Cohen; Allan J. ...

Cited by 100 • Published online • All 2 versions

Standardized flash controller

A. Ban. • US Patent 5,799,188, 1998 - Google Patents

... would then execute the erase procedure for that block by 5 writing an Erase (hex 20) command anywhere **within** the **flash** block to ... Identify command using the Intel 28F008 chip, standardized controller would report the num-ber of chips present, their **interleaving** factor, and ...

Cited by 89 • Published online • All 2 versions

Method of pipelining sequential writes in a flash memory

ML. Fandrich, RJ. Duranta. • US Patent 5,619,947, 1996 - Google Patents

... US005519847A [A] Patent Number: [45] Date of Patent: 5,619,947 May 21, 1996 [54] METHOD OF PIPELINING SEQUENTIAL WRITES IN A FLASH MEMORY [75] Inventors: Mickey L. Fandrich, Placerville; Richard J. Duranta, Offutt Heights; Rodney R. Rozman, Placerville, all of ...

Cited by 63 • Published online • All 2 versions

Flash memory architecture implementing simultaneously programmable multiple flash memory banks that are host compatible

P. Esauhin. • US Patent 6,721,843, 2004 - Google Patents

... overhead data, thereby emulating the size of a data field typically available in commercial hard disks. FIG. 1 depicts a non-volatile memory array 65 **within** a **flash** memory device. A collection of Physical Sectors or Pages 108, ...

Cited by 16 • Published online • All 2 versions

USB smart switch with packet re-ordering for interleaving among multiple flash-memory endpoints aggregated as a single virtual USB endpoint

BW. Chen, HY. Chou. • US Patent 7,673,019, 2006 - Google Patents

... 4, 2006 [54] USB SMART SWITCH WITH PACKET RE-ORDERING FOR INTERLEAVING AMONG MULTIPLE FLASH-MEMORY ENDPOINTS AGGREGATED AS A SINGLE VIRTUAL USB ENDPOINT [75] Inventors: Ben Wei Chen, Fremont, CA (US); Horng-Yee Chou, Palo Alto ...

Cited by 18 • Published online • All 2 versions

Method and apparatus for storing location identification information within non-volatile memory devices

MA. Anagnostou. • US Patent 6,027,689, 2001 - freepatentonline.com

... In fact, generally, a controller semiconductor device coupled between the host (in the computer system) and the **flash** devices translates the logical block address (LBA) into a physical block address (PBA) and uses the latter to access the data file **within** **flash** memory. ...

Cited by 56 • Published online • Abstract • All 2 versions

Hydra: A block-mapped parallel flash memory solid-state disk architecture

YJ. Seong, EH. Nam, JH. Yoon, H. Kim. • IEEE Transactions on ..., 2010 - cs.mcgill.ca

... 3.1 Bus-Level and Chip-Level **Interleaving** The Hydra SSD uses **interleaving** over multiple **flash** memory buses to overcome the bandwidth limitation of the **flash** memory bus. In the bus-level **interleaving**, sectors **within** a superblock are distributed in a round-robin manner. ...

Cited by 11 • Published online • All 2 versions

Energy efficient software-based self-test for wireless sensor network nodes

PDF from mendeley

H. Zhang, Z. Zhao. • VLSI Test Symposium, 2006. ... 2006 - ieee.computer-ieee.org

... 8 RAM W0 (ten blocks - 5Kbytes) 9 RAM R0 (ten blocks - 5Kbytes) A RF Initialization B RF packets sending (4 packets) Figure 18 shows the current measurement result before and after time interval between FLASH erase and RAM testing **within** embedded memories in the ...

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